

First characterizations of thin SOI and epitaxial n-in-p sensors

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We will present the results of first leakage-current and capacitance measurements of our 75 and 150 micron thin SOI production of n-in-p sensors before irradiation. They exhibit low dark currents and depletion voltages.

A comparison between the performance of the standard and a reduced guard ring structure will be shown.

Furthermore, the RD50 production of thin epitaxial n-in-p sensors, made by CIS, was characterized.

Infrared pictures reveal signs of break downs in the inner guard rings as well as in the active area close to the bias ring.

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